

**Surface Mount Monolithic Integrated PIN Diode Chip:**  
0604 Unconnected Double Tee

**MADP-064908-131000**  
**Sumount™ PIN Chip V1**

**Features**

- No Wirebonds Required
- Rugged Silicon-Glass Construction
- Silicon Nitride Passivation & Polymer Scratch Protection
- Ultra-Low Parasitic Capacitance and Inductance
- Higher RF C.W. Power Handling
- Better Performance than Alternative Packaged Devices

**Description and Applications**

This device is a Silicon-Glass PIN diode chip fabricated with M/A-COM's patented HMIC process. This 8.0 μm I-region length device features 6 silicon pedestals embedded in a low loss, low dispersion glass. The diodes are formed on the top of a pedestal and connections to the backside of the device are facilitated by making the pedestal sidewalls electrically conductive. Selective backside metallization is applied producing a surface mount device. The topside is fully encapsulated with silicon nitride and has an additional polymer layer for scratch protection. These protective coatings prevent damage to the junction and the anode air-bridge during handling and assembly. The vertical Silicon Diode topology provides for a highly efficient heat transfer medium.

These packageless devices are suitable for usage in Higher ( 3 W Avg ) Incident Power Switches. Small Parasitic Inductance and Excellent RC Constant make the devices ideal for Absorptive SPST, Reflective SP2T Switches, and Attenuator Circuits, where higher P1db and Power Handling values are required.

Dim	Inches		Millimeters	
	Min.	Max.	Min.	Max.
A	0.060	0.062	1.524	1.575
B	0.036	0.038	0.914	0.965
C	0.004	0.008	0.102	0.203
D	0.011	0.012	0.279	0.305

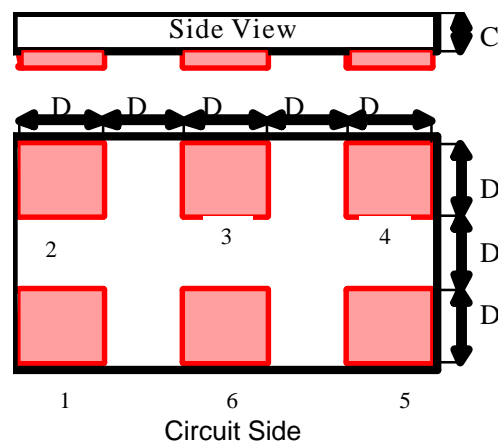
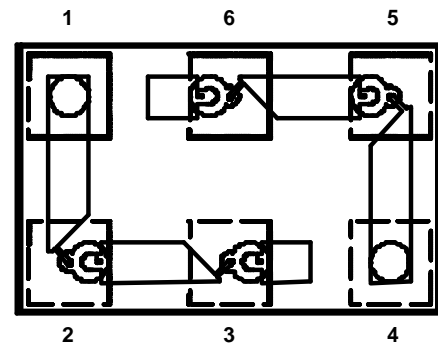
**Absolute Maximum Ratings<sup>1</sup>**

@ T<sub>A</sub> = +25 °C (unless otherwise specified)

Parameter	Absolute Maximum
Forward Current	250 mA
Reverse Voltage	I -100 V I
Operating Temperature	-55 °C to +125 °C
Storage Temperature	-55 °C to +150 °C
Junction Temperature	+175 °C
C.W. Incident Power (dBm)	+35 dBm
Mounting Temperature	+300 °C for 10 seconds

1. Operation of this device above any one of these parameters may cause permanent damage.

**0604 Case Style - ODS-1310 (Topview)**



1. Backside Metal: 0.1microns thick.
2. Shaded Areas Indicate Backside Ohmic Gold Contacts.

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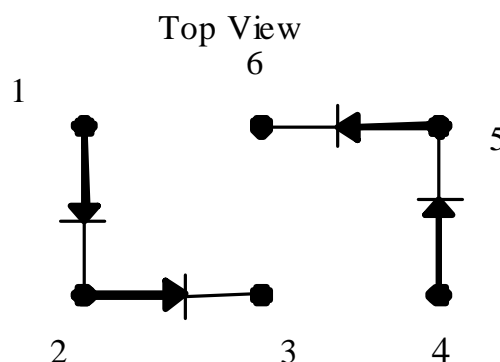
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**Electrical Specifications @ +25 °C, per Diode Junction**

Symbol	Conditions	Units	Min.	Typ.	Max.
$C_T$	-40 V, 1 MHz <sup>1</sup>	pF		0.05	0.07
$C_T$	-40 V, 1 GHz <sup>1,3</sup>	pF		0.04	0.06
$R_S$	10 mA, 1 GHz <sup>2,3</sup>	$\Omega$		5.0	
$V_F$	10 mA	V		0.83	1.00
$V_R$	-10 $\mu$ A	V	-70	-100	
$I_R$	-70 V	$\mu$ A		-0.1	-10
$T_L$	+ 10 mA / -6 mA	ns		200	
$\theta_{TH}$	1A / 10 mA	$^{\circ}$ C / W		150	

1. Total capacitance,  $C_T$ , is equivalent to the sum of Junction Capacitance,  $C_j$ , and Parasitic Capacitance,  $C_{par}$ .
2. Series resistance  $R_S$  is equivalent to the total diode resistance :  $R_s = R_j$  ( Junction Resistance) +  $R_c$  ( Ohmic Resistance)
3.  $R_s$ ,  $C_T$ ,  $T_L$ ,  $\theta_{TH}$  are measured on an HP4291A Impedance Analyzer with die mounted in an ODS-186 package with Sn 60/Pb 40 Solder

**Equivalent 0604 Style Double Tee Equivalent Circuit**



**Notes:**

1. Ports 2 and 5 have a Connected Cathode-Anode Node.
2. Ports 1,3,4, and 6 Have a Singular, Un-Connected Node.

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## Assembly Guidelines

### Handling

All semiconductor chips should be handled with care to avoid damage or contamination from perspiration and skin oils. The use of plastic tipped tweezers or vacuum pickups is strongly recommended for individual components. Bulk handling should insure that abrasion and mechanical shock are minimized.

### Bonding

Attachment to a circuit board is made simple through the use of surface mount technology. Mounting pads are conveniently located on the bottom surface of these devices and are removed from the active junction locations. These devices are well suited for solder attachment onto hard and soft substrates. The use of 80 Au / 20 Sn or Sn 60 / Pb 40 solder is recommended. Conductive silver epoxy for die attachment, approximately 2 mils in uniform thickness may also be used for lower Incident power applications ( < 1 W Average Power ).

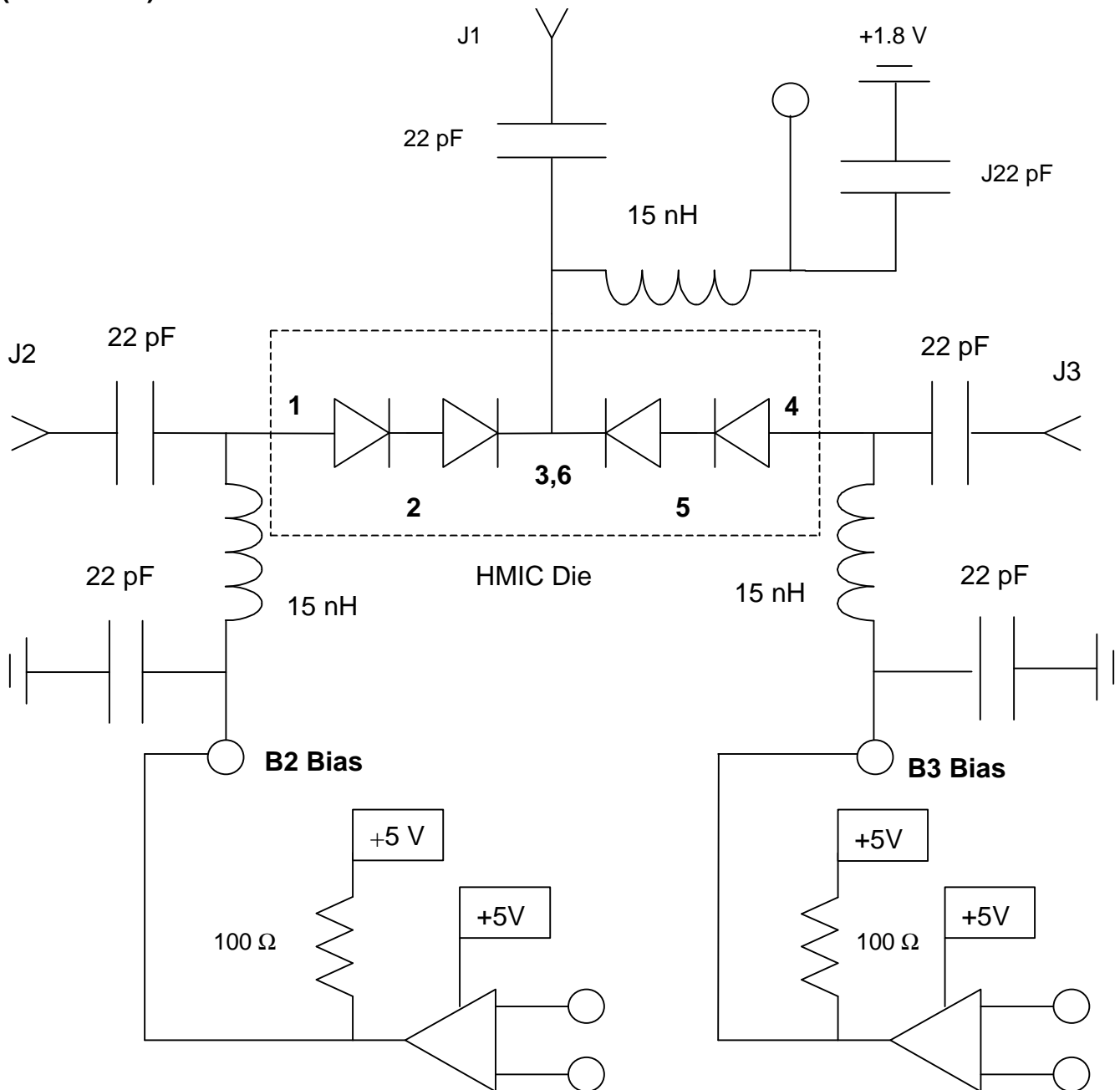
When soldering these devices to a hard substrate, hot gas die bonding is preferred. We recommend utilizing a vacuum tip and force of 60 to 100 grams applied normal to the top surface of the device. When soldering to soft substrates, it is recommended to use a lead-tin interface at the circuit board mounting pads. Position the die so that its mounting pads are aligned with the circuit board mounting pads and reflow the solder by heating the circuit trace near the mounting pad while applying 60 to 100 grams of force perpendicular to the top surface of the die. The solder joint must Not be made one at a time, creating un-equal heat flow and thermal stress. Solder reflow should Not be performed by causing heat to flow through the top surface of the die. Since the HMIC glass is transparent, the edges of the mounting pads closest to each other can be visually inspected through the die after attach is completed.

A typical profile for a Sn 60/ Pb 40 Soldering process is provided in [Application Note, " M538 "](#),  
[" Surface Mounting Instructions "](#) on the MA-COM website [www.macom.com](http://www.macom.com)

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**Circuit Applications : SP2T All Series Reflective Switch with +5V and TTL Logic Control ( 2- 18 GHz )**



SN7406, SN7416 TTL Open Collector Gate Driver ( X2 )

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**RF Truth Table for Reflective SP2T using Singular Power Supply: + 5V, + I Only**

RF State	B2 Diode Bias	B3 Diode Bias
J1 – J2 Low Loss & J1– J3 Isolation	+ 3.6 V @ + 14 mA	+0.5 V @ 0 mA
J1 – J3 Low Loss & J1–J2 Isolation	+0.5 V @ 0 mA	+ 3.6 V @ + 14 mA

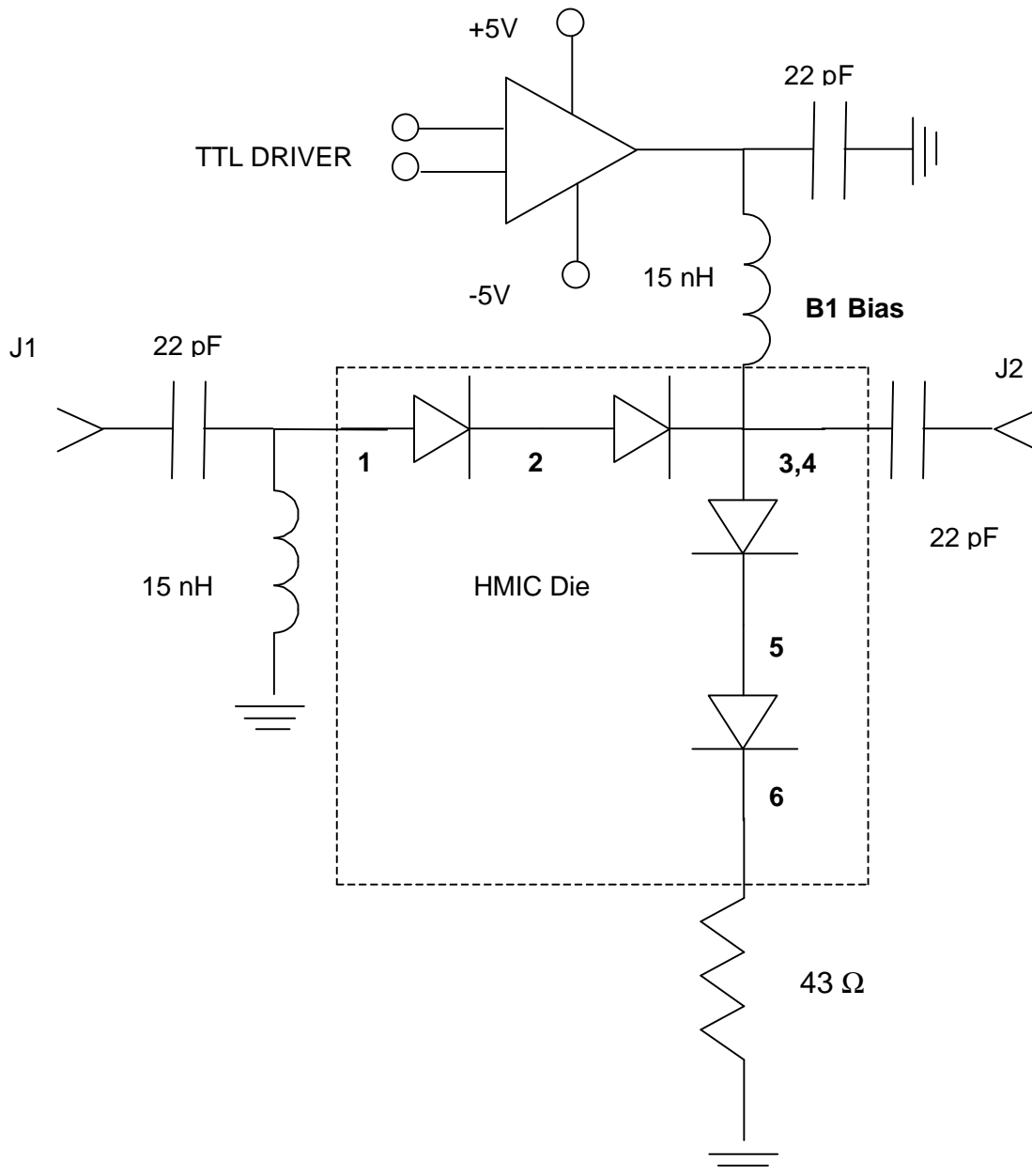
**Notes:**

1. Diode Forward Voltage Differential (  $\Delta V_f$  ) @ 15 mA = 0.9 V
2. Insertion Loss Diode Bias = ( + 5V – (2)\* 0.9 V – 1.8 V ) / ( 100  $\Omega$  ) = 14 mA
3. Off Isolation Diode Back Bias Voltage = | – ( +1.8 V – 0.5 V ) | = | – 1.3 V |.

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**Circuit Applications : SPST All Series Absorptive Switch with +5V and TTL Logic Control**  
**( 2- 18 GHz )**



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**RF Truth Table for Absorptive SPST using + 5V, – 5V Power Supplies**

RF State	TTL Value	B1 Diode Bias
J1 – J2 Low Loss	0	- 1.8 V @ -20 mA
J1–J2 Isolation	1	+ 2.7 V @ + 20 mA

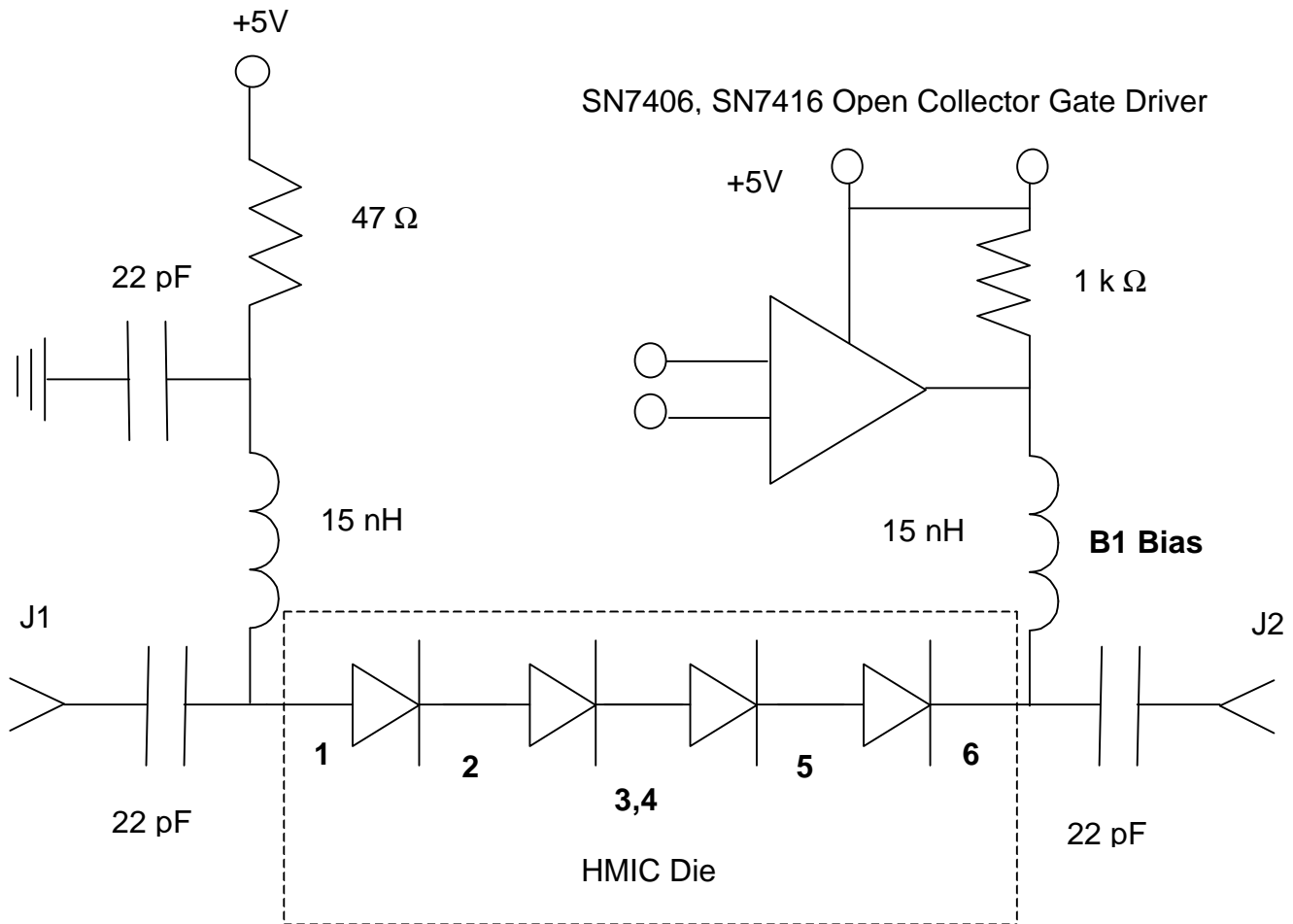
**Notes:**

1. Diode Forward Voltage Differential (  $\Delta V_f$  ) @ 20 mA = 0.9 V
2. Diode  $R_s$  @ 20 mA = 3.5  $\Omega$
3. Insertion Loss Diode Bias = ( – 1.8 V ) @ -20 mA from a Constant Current Source
4. Off Isolation Diode Back Bias Voltage through (2) Diodes = | – ( +2.7 V – 0 V ) | = | – 2.7 V |.

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**Circuit Applications : SPST All Series Reflective Switch with +5V and TTL Logic Control ( 2- 18 GHz )**



**RF Truth Table for Reflective SPST using Singular Power Supply: + 5V, + I Only**

RF State	TTL Value	B1 Diode Bias
J1 – J2 Low Loss	0	+ 0.5 V @ +20 mA
J1–J2 Isolation	1	+5.0 V @ 0 mA



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MADP-064908 SPICE Model

PinDiodeModel	wBv=80 V
NLPINM1	wPmax=3.0 W
Is=1.0E-14 A	Ffe=1.0
Vi=0.0 V	
Un=900 cm <sup>2</sup> /V-sec	
Wi=7.5 um	
Rr=20 K Ohm	
Cmin=0.05 pF	
Tau=0.20 usec	
Rs=0.1 Ohm	
Cj0=0.06 pF	
Vj=0.7 V	
M=0.5	
Fc=0.5	
Imax=1.0E+6 A/m <sup>2</sup>	
Kf=0.0	
Af=1.0	

**Equivalent per Diode Schematic**

